

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) ~~AA-A~~ A Johnsen-Rahbek effect electrostatic chuck comprising:

a substrate having a wafer-installing face and an opposed back face, an electrostatic chucking electrode buried in said substrate, and an insulating layer provided on said back face of said substrate;

said substrate further comprising a dielectric layer including at least said wafer-installing face and surrounding said electrostatic chucking electrode;

wherein said insulating layer comprises an insulating material having a larger volume resistivity ~~larger~~ than that of said dielectric layer;

wherein an area of said dielectric layer that contacts said electrostatic chucking electrode has a higher volume resistivity than the remainder of said dielectric layer;  
and

wherein leakage current originating from said electrostatic chucking electrode is reduced and inhibited from flowing through said insulating layer.

2. (Original) The electrostatic chuck set forth in claim 1, wherein said electrostatic chucking electrode further comprises at least two electrodes having different load potentials.

3. (Original) The electrostatic chuck set forth in claim 1, further comprising an electrically conductive member provided on said back face of said substrate and adapted to release heat inputted from said wafer-installing face to said conductive member.

4. (Original) The electrostatic chuck set forth in claim 1, wherein said electrostatic chucking electrode comprises a net or punched metal.
5. (Original) The electrostatic chuck set forth in claim 1, wherein said electrostatic chucking electrode comprises molybdenum metal or a molybdenum alloy.
6. (Currently Amended) An electrostatically attracting structure comprising:  
    ~~an~~ a Johnsen-Rahbek effect electrostatic chuck for attracting a wafer and an electrically conductive member joined to a back face of said electrostatic chuck;  
    said electrostatic chuck comprising a substrate having a wafer-installing face and an opposed back face, and an -electrostatic chucking electrode buried in said substrate;  
    said substrate further comprising a dielectric layer including at least said wafer-installing face and surrounding said -electrostatic chucking electrode, and an insulating layer provided on said back face of said substrate;  
    wherein said insulating layer comprises an insulating material having a larger volume resistivity ~~larger than that of the said dielectric layer;~~  
    wherein an area of said dielectric layer that contacts said electrostatic chucking electrode has a higher volume resistivity than the remainder of said dielectric layer;  
    and  
    wherein leakage current originating from said electrostatic chucking electrode is reduced and inhibited from flowing through said insulating layer toward said electrically conductive member,
7. (Original) The electrostatically attracting structure set forth in claim 6, wherein said electrostatic chucking electrode further comprises at least two electrodes having different load potentials.

8. (Original) The electrostatically attracting structure set forth in claim 6, wherein said electrostatic chucking electrode comprises a net or punched metal.

9. (Original) The electrostatically attracting structure set forth in claim 6, wherein said electrostatic chucking electrode comprises molybdenum metal or a molybdenum alloy.

10. (Original) The electrostatically attracting structure set forth in claim 6, wherein said electrically conductive member comprises a cooling member.

11. (Currently Amended) ~~An~~A Johnsen-Rahbek effect electrostatic chuck comprising:

a dielectric layer defining a wafer-installing face and having an opposed back face;

at least two electrostatic chucking electrodes having different load potentials buried in and surrounded by said dielectric layer; and

an insulating layer co-fired with said dielectric layer and provided on said back face of said dielectric layer, said insulating layer comprising an insulating material having a larger volume resistivity ~~larger than~~ that of said dielectric layer;

wherein an area of said dielectric layer that contacts each said at least two electrostatic chucking electrodes has a higher volume resistivity than the remainder of said dielectric layer; and

wherein leakage current originating from said at least two electrostatic chucking electrodes is reduced and inhibited from flowing through said insulating layer.

12. (Original) The electrostatic chuck set forth in claim 11, further comprising an electrically conductive member provided on said insulating layer and adapted to release heat inputted from said wafer-installing face to said conductive member.

13. (Currently Amended) The electrostatic chuck set forth in claim 11, wherein said at least two electrostatic chucking electrodes comprise a net or punched metal.

14. (Currently Amended) The electrostatic chuck set forth in claim 11, wherein said at least two electrostatic chucking electrodes comprise molybdenum metal or a molybdenum alloy.

15. (Currently Amended) An electrostatically attracting structure comprising:  
~~an a Johnsen-Rahbek effect~~ electrostatic chuck for attracting a wafer and an electrically conductive member joined to a rear face of said electrostatic chuck;  
said electrostatic chuck comprising a dielectric layer defining a wafer-installing face and having an opposed back face, at least two electrostatic chucking electrodes having different load potentials buried in and surrounded by said dielectric layer, and an insulating layer co-fired with said dielectric layer and provided on said back face of said dielectric layer, said insulating layer defining said rear face of said electrostatic chuck, and said insulating layer comprising an insulating material having a larger volume resistivity ~~larger than~~ that of said dielectric layer;  
wherein an area of said dielectric layer that contacts each said at least two electrostatic chucking electrodes has a higher volume resistivity than the remainder of said dielectric layer; and  
wherein leakage current originating from said at least two electrostatic chucking electrodes is reduced and inhibited from flowing through said insulating layer toward said electrically conductive member.

16. (Currently Amended) The electrostatically attracting structure set forth in claim 15, wherein said at least two electrostatic chucking electrodes comprise a net or punched metal.

17. (Currently Amended) The electrostatically attracting structure set forth in claim 15, wherein said at least two electrostatic chucking electrodes comprise molybdenum metal or a molybdenum alloy.

18. (Original) The electrostatically attracting structure set forth in claim 15, wherein said electrically conductive member comprises a cooling member.